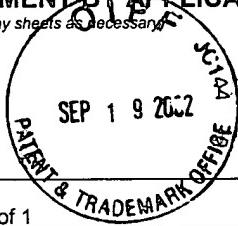


Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
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Complete if Known

<b>Application Number</b>	09/483881
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<b>First Named Inventor</b>	Ahn, Kie
<b>Group Art Unit</b>	2812
<b>Examiner Name</b>	Unknown

Sheet 1 of 1

Attorney Docket No: 00303.672US1

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*[Signature]*

DATE CONSIDERED

11-19-02